Abstracts

W-Band GaAs MESFET Frequency Doubler

J. Geddes, V. Sokolov and A. Contolatis. "W-Band GaAs MESFET Frequency Doubler." 1987 Microwave and Millimeter-Wave Monolithic Circuits Symposium Digest 87.1 (1987 [MCS]): 7-10.

A monolithic W-band frequency doubler has been developed using submicron gate length GaAs MESFETs fabricated on ion implanted material. The frequency doubler provides a power output of over 4.0 mW at 94 GHz with an input drive of 70 mW at 47 GHz. To of a MESFET our knowledge this is the first report frequency doubler operating at W-band.

❑ Return to main document.

Click on title for a complete paper.